

Notice of References Cited	Application/Control No. 10/602,194	Applicant(s)/Patent Under Reexamination ONO, YOSHI	
	Examiner Khiem D. Nguyen	Art Unit 2823	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	"In-situ surface preparation of InP-based semiconductors prior to direct UVCVD silicon nitride deposition for passivation purposes" How Kee Chun, L.S.; Courant, J.L.; Ossart, P.; Post, G.; Indium Phosphide and Related Materials, April 1996 pages 412-415.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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